

2SD965

Rev.E Mar.-2016

TO-92

NPN

Silicon NPN transistor in a TO-92 Plastic Package.

LOW $V_{CE(sat)}$

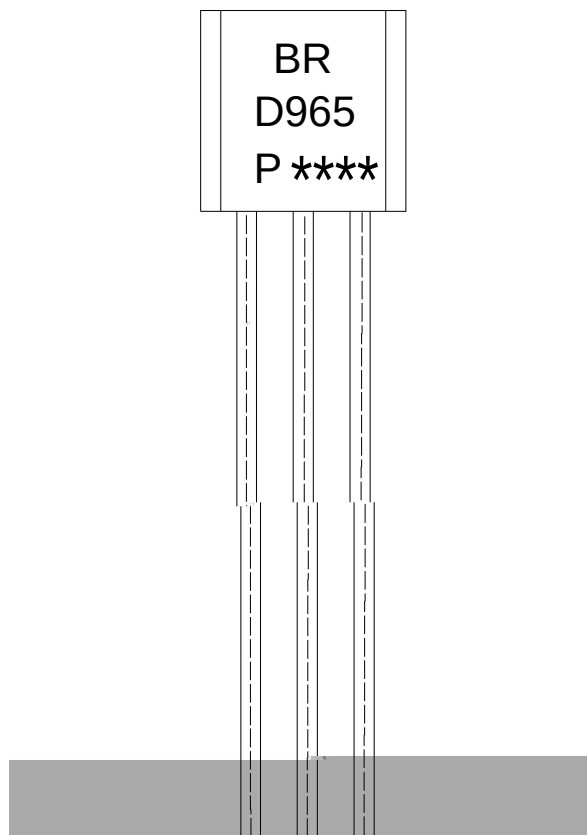
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	5.0	A
Collector Current – Continuous(Pulse)	I_{CP}	8.0	A
Collector Power Dissipation	P_C	750	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	20			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=10 A$ $I_C=0$	7.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=10V$ $I_E=0$			0.1	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=7.0V$ $I_C=0$			0.1	A
DC Current Gain	$h_{FE(1)}$	$V_{CE}=2.0V$ $I_C=0.5A$	180		1000	
	$h_{FE(2)}$	$V_{CE}=2.0V$ $I_C=2.0A$	150			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=3.0A$ $I_B=0.1A$			1.0	V
Transition Frequency	f_T	$V_{CE}=6.0V$ $I_C=50mA$		150		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=20V$ $I_E=0$ $f=1.0MHz$			50	pF

/ Marking Instructions



BR:

D965

P: h_{FE}

Note:

BR: Company Code.

D965: Product Type.

P: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255±5

, Duration:5±0.5sec.
3. Cooling Speed: 2~10

/sec.

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension (unit mm3)		
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	Bag6	re10	T8(600023	TBag14(0,59075(	13384(237×172×79(0275(	9173560×245